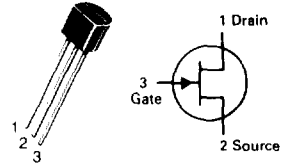


J111 thru J113

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET CHOPPER TRANSISTORS

N-CHANNEL — DEPLETION

Refer to MPF4391 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V _{DG}	-35	Vdc
Gate-Source Voltage	V _{GS}	-35	Vdc
Gate Current	I _G	50	mA
Total Device Dissipation (at T _A = 25°C Derate above 25°C)	P _D	350 2.8	mW mW/°C
Lead Temperature	T _L	300	°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I _G = -1.0 μA)	V _{(BR)GSS}	35	—	Vdc
Gate Reverse Current (V _{GS} = -15 V)	I _{GSS}	—	-1.0	nA
Gate Source Cutoff Voltage (V _{DS} = 5.0 V, I _D = 1.0 μA)	V _{GS(off)}	J111 -3.0 J112 -1.0 J113 -0.5	-10 -5.0 -3.0	V
Drain-Cutoff Current (V _{DS} = 5.0 V, V _{GS} = -10 V)	I _{D(off)}	—	1.0	nA

ON CHARACTERISTICS

Zero-Gate-Voltage Drain Current* (V _{DS} = 15 V)	I _{DSS}	J111 20 J112 5.0 J113 2.0	— — —	mA
Static Drain-Source On Resistance (V _{DS} = 0.1 V)	r _{DS(on)}	J111 — J112 — J113 —	30 50 100	Ohms
Drain Gate and Source Gate On-Capacitance (V _{DS} = V _{GS} = 0, f = 1.0 MHz)	C _{dg(on)} + C _{sg(on)}	—	28	pF
Drain Gate Off-Capacitance (V _{GS} = -10 V, f = 1.0 MHz)	C _{dg(off)}	—	5.0	pF
Source Gate Off-Capacitance (V _{GS} = -10 V, f = 1.0 MHz)	C _{sg(off)}	—	5.0	pF

*Pulse Width = 300 μs, Duty Cycle = 3.0%.